英飞凌 TRENCHSTOP™ IGBT6，带软恢复、快速恢复反并联 Rapid 二极管

特性

- V_{CE} = 650 V
- I_C = 10 A
- 极低 $V_{CE(sat)}$ 1.5V（典型值）
- 最高结温 T_{vjmax} = 175°C
- 短路耐受时间 3 µs
- 参数分布紧密
- 高稳健性、温度稳定性
- 低 $V_{CE(sat)}$ 和正温度系数
- 低栅极电荷 Q_G
- 无铅引脚镀层；符合 RoHS 标准
- 带软恢复和快速恢复的反并联二极管
- 完整的产品范围和 PSpice 模型： http://www.infineon.com/igbt/



Lead-Free

Green

Halogen-Free

RoHS

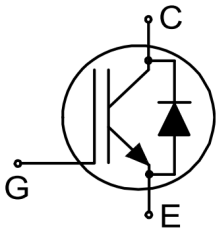
潜在应用

- 通用驱动器（GPD）
- 空调
- 其他大型家用电器
- 其他小型家用电器

产品验证

- 符合 JEDEC47/20/22 相关测试的工业应用要求

描述



Type	Package	Marking
IKA10N65ET6	PG-TO220-3 FP	K10EET6

本数据手册的原文使用英文撰写。为方便起见，英飞凌提供了译文；由于翻译过程中可能使用了自动化工具，英飞凌不保证译文的准确性。为确认准确性，请务必访问 infineon.com 参考最新的英文版本（控制文档）。

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1 封装

表 1 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Isolation test voltage RMS	V_{isol}	f = +50/+60 Hz, t = 1 min			2500	V
Internal emitter inductance measured 5 mm (0.197 in) from case	L_E			7.0		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature		wave soldering 1.6mm (0.063in.) from case for 10s			260	°C
Mounting torque, M3 screw Maximum of mounting processes: 3	M				0.5	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				65	K/W

2 IGBT

表 2 最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}	T_{vj} ≥ 25 °C		650	V
DC collector current, limited by T_{vjmax} *1)*	I_C		T_h = 25 °C	25	A
			T_h = 100 °C	16	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}			42.5	A
Turn-off safe operating area		V_{CE} ≤ 650 V, T_{vj} ≤ 175 °C		42.5	A
Gate-emitter voltage	V_{GE}			±20	V
Transient gate-emitter voltage	V_{GE}	t_p ≤ 10 µs, D < 0.010		±30	V
Short-circuit withstand time	t_{SC}	V_{CC} ≤ 360 V, V_{GE} = 15 V, Allowed number of short circuits < 1000, Time between short circuits ≥ 1.0 s, T_{vj} = 150 °C		3	µs
Power dissipation	P_{tot}		T_h = 25 °C	32.5	W
			T_h = 100 °C	16.2	

1) 受最高结温的限制。适用于 TO220 标准封装。

表 3 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter breakdown voltage[1)]	V_{BRCES}	I_C = 0.1 mA, V_{GE} = 0 V		650			V
Collector-emitter saturation voltage	V_{CEsat}	I_C = 8.5 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.5	1.9	V
			T_{vj} = 125 °C		1.65		
			T_{vj} = 150 °C		1.75		
Gate-emitter threshold voltage	V_{GEth}	I_C = 0.15 mA, V_{CE} = V_{GE}		4.8	5.6	6.4	V
Zero gate-voltage collector current	I_{CES}	V_{GE} = 0 V, V_{CE} = 650 V	T_{vj} = 25 °C			30	µA
			T_{vj} = 150 °C		360		
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V				100	nA
Transconductance	g_{fs}	I_C = 8.5 A, V_{CE} = 20 V, T_{vj} ≥ 25 °C			8.7		S
Short-circuit collector current	I_{SC}	V_{CC} ≤ 360 V, V_{GE} = 15 V, t_{SC} ≤ 3 µs, Allowed number of short circuits < 1000 , Time between short circuits ≥ 1.0 s , T_{vj} = 150 °C			80		A
Input capacitance	C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1000 kHz			790		pF
Output capacitance	C_{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1000 kHz			41		pF
Reverse transfer capacitance	C_{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1000 kHz			12		pF
Gate charge	Q_G	I_C = 8.5 A, V_{GE} = 15 V			27		nC
Turn-on delay time	t_{don}	V_{CE} = 400 V, V_{GE} = 15 V, R_{Gon} = 47.0 Ω, R_{Goff} = 47.0 Ω, L_σ = 30 nH, C_σ = 150 pF	T_{vj} = 25 °C, I_C = 8.5 A		30		ns
			T_{vj} = 150 °C, I_C = 8.5 A		27		
Rise time (inductive load)	t_r	V_{CE} = 400 V, V_{GE} = 15 V, R_{Gon} = 47.0 Ω, R_{Goff} = 47.0 Ω, L_σ = 30 nH, C_σ = 150 pF	T_{vj} = 25 °C, I_C = 8.5 A		18		ns
			T_{vj} = 150 °C, I_C = 8.5 A		18		
Turn-off delay time	t_{doff}	V_{CE} = 400 V, V_{GE} = 15 V, R_{Gon} = 47.0 Ω, R_{Goff} = 47.0 Ω, L_σ = 30 nH, C_σ = 150 pF	T_{vj} = 25 °C, I_C = 8.5 A		106		ns
			T_{vj} = 150 °C, I_C = 8.5 A		123		
Fall time (inductive load)	t_f	V_{CE} = 400 V, V_{GE} = 15 V, R_{Gon} = 47.0 Ω, R_{Goff} = 47.0 Ω, L_σ = 30 nH, C_σ = 150 pF	T_{vj} = 25 °C, I_C = 8.5 A		46		ns
			T_{vj} = 150 °C, I_C = 8.5 A		72		

（表格续下页……）

表 3　　（续）特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-on energy	E_{on}	V_{CE} = 400 V, V_{GE} = 15 V, R_{Gon} = 47.0 Ω, R_{Goff} = 47.0 Ω, L_σ = 30 nH, C_σ = 150 pF	T_{vj} = 25 °C, I_C = 8.5 A		0.2		mJ
			T_{vj} = 150 °C, I_C = 8.5 A		0.22		
Turn-off energy	E_{off}	V_{CE} = 400 V, V_{GE} = 15 V, R_{Gon} = 47.0 Ω, R_{Goff} = 47.0 Ω, L_σ = 30 nH, C_σ = 150 pF	T_{vj} = 25 °C, I_C = 8.5 A		0.07		mJ
			T_{vj} = 150 °C, I_C = 8.5 A		0.13		
Total switching energy	E_{ts}	V_{CE} = 400 V, V_{GE} = 15 V, R_{Gon} = 47.0 Ω, R_{Goff} = 47.0 Ω, L_σ = 30 nH, C_σ = 150 pF	T_{vj} = 25 °C, I_C = 8.5 A		0.27		mJ
			T_{vj} = 150 °C, I_C = 8.5 A		0.35		
IGBT thermal resistance, junction to case	R_{thjc}					4.6	K/W
IGBT thermal resistance, junction to heat sink	R_{thjh}					4.60	K/W
Operating junction temperature	T_{vj}			-40		175	°C

1)　使用滤波器网络进行测量。

注：　　电气特性，在 T_{vj} = 25°C 条件下测得，除非另有规定。

3　二极管

表4　　最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}	T_{vj} ≥ 25 °C		650	V
Diode forward current, limited by T_{vjmax} *1)*	I_F		T_h = 25 °C	19.5	A
			T_h = 100 °C	11	
Diode pulsed current, limited by T_{vjmax}	I_{Fpuls}			42.5	A

1)　受最高结温的限制。适用于 TO220 标准封装。

表5 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode forward voltage	V_F	I_F = 8.5 A	T_{vj} = 25 °C		1.45	1.9	V
			T_{vj} = 125 °C		1.43		
			T_{vj} = 150 °C		1.39		
Reverse leakage current	I_R	V_R = 650 V	T_{vj} = 25 °C			30	µA
			T_{vj} = 150 °C		360		
Diode reverse recovery time	t_{rr}	V_R = 400 V	T_{vj} = 25 °C, I_F = 8.5 A, $-di_F/dt$ = 450 A/µs		51		ns
			T_{vj} = 150 °C, I_F = 8.5 A, $-di_F/dt$ = 450 A/µs		92		
Diode reverse recovery charge	Q_{rr}	V_R = 400 V	T_{vj} = 25 °C, I_F = 8.5 A, $-di_F/dt$ = 450 A/µs		0.206		µC
			T_{vj} = 150 °C, I_F = 8.5 A, $-di_F/dt$ = 450 A/µs		0.455		
Diode peak reverse recovery current	I_{rrm}	V_R = 400 V	T_{vj} = 25 °C, I_F = 8.5 A, $-di_F/dt$ = 450 A/µs		5.7		A
			T_{vj} = 150 °C, I_F = 8.5 A, $-di_F/dt$ = 450 A/µs		7.8		
Diode peak rate of fall of reverse recovery current	dI_{rr}/dt	V_R = 400 V	T_{vj} = 25 °C, I_F = 8.5 A, $-di_F/dt$ = 450 A/µs		-440		A/µs
			T_{vj} = 150 °C, I_F = 8.5 A, $-di_F/dt$ = 450 A/µs		-205		
Diode thermal resistance, junction to case	R_{thjc}					6.4	K/W
Diode thermal resistance, junction to heat sink	R_{thjh}					6.40	K/W
Operating junction temperature	T_{vj}			-40		175	°C

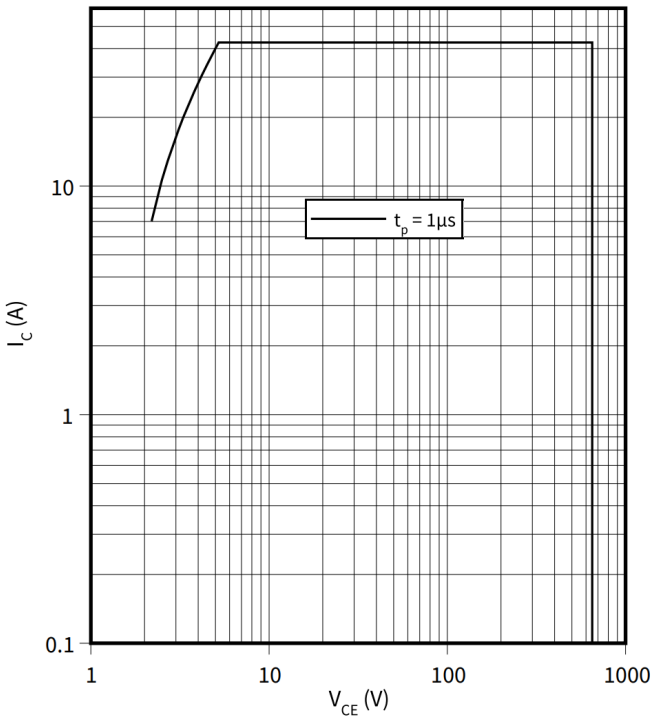
注： 为了获得最佳的使用寿命和可靠性，英飞凌建议运行条件不超过本数据手册中所述最大额定值的80%。

4 特性图

Forward bias safe operating area, IGBT

$I_C = f(V_{CE})$

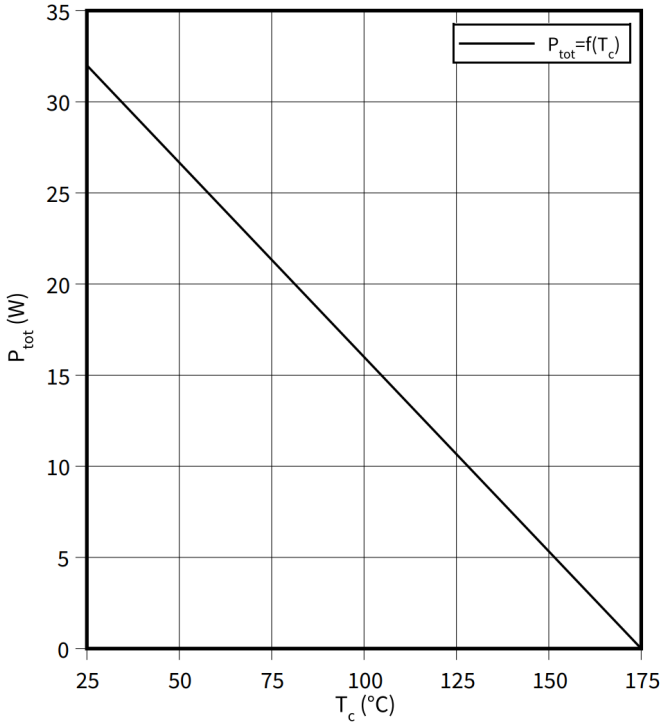
$D = 0$, $T_{vj} \leq 175$ °C, $V_{GE} \geq 15$ V, $T_h = 25$ °C



Power dissipation as a function of case temperature, IGBT

$P_{tot} = f(T_c)$

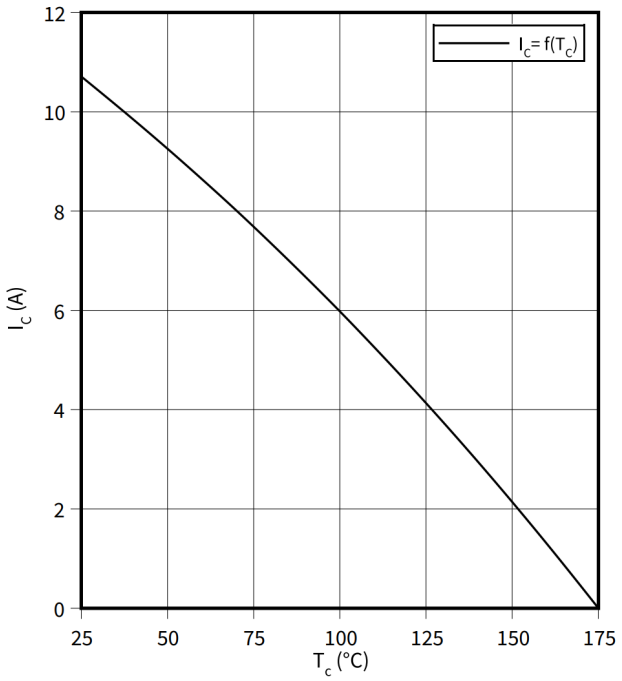
$T_{vj} \leq 175$ °C



Collector current as a function of case temperature, IGBT

$I_C = f(T_c)$

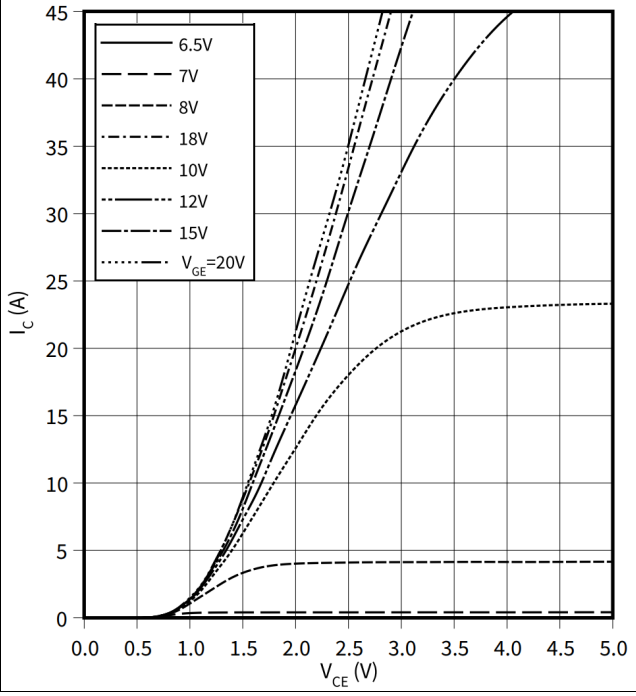
$T_{vj} \leq 175$ °C, $V_{GE} \geq 15$ V



Typical output characteristic, IGBT

$I_C = f(V_{CE})$

$T_{vj} = 25$ °C

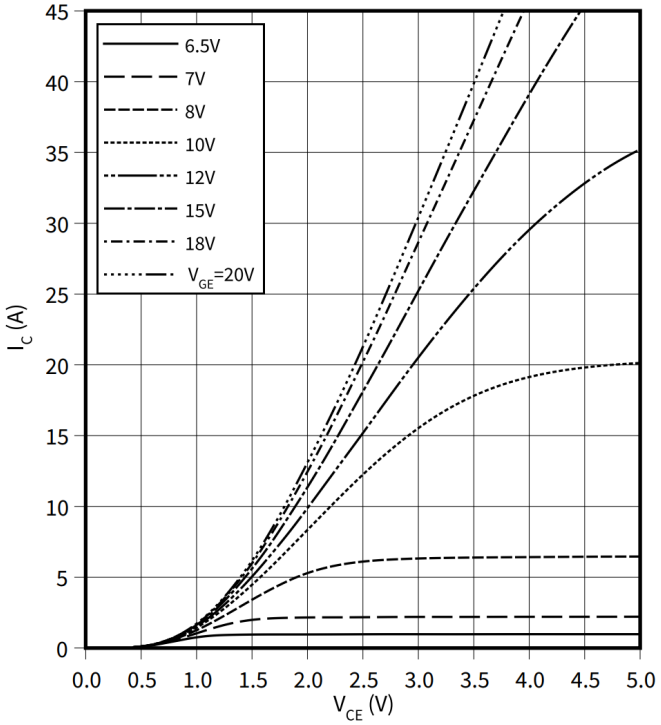


4. 特性图

Typical output characteristic, IGBT

$I_C = f(V_{CE})$

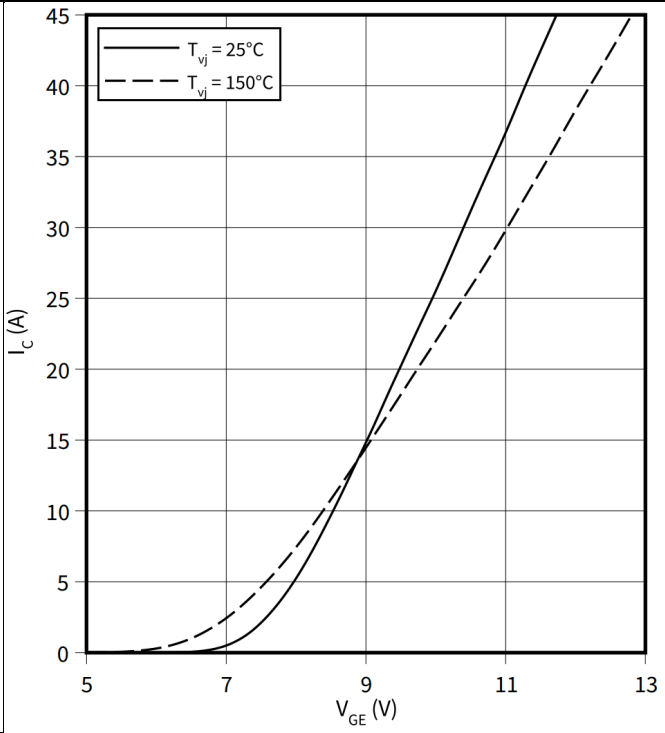
$T_{vj} = 150\ °C$



Typical transfer characteristic, IGBT

$I_C = f(V_{GE})$

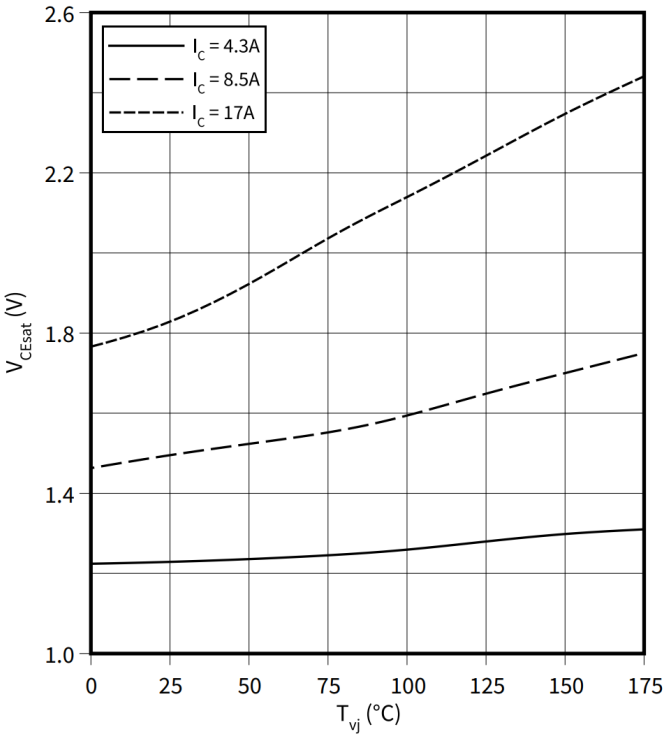
$V_{CE} = 50\ V$



Typical collector-emitter saturation voltage as a function of junction temperature, IGBT

$V_{CEsat} = f(T_{vj})$

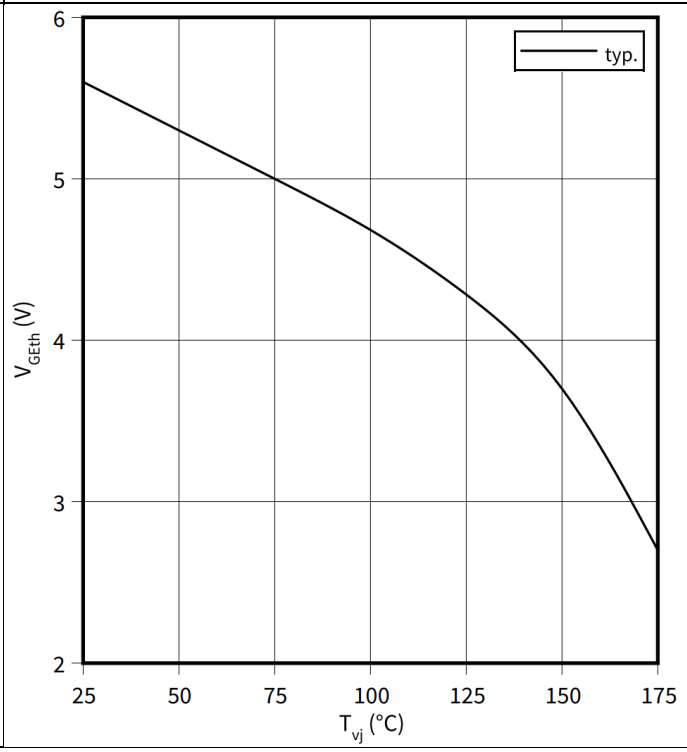
$V_{GE} = 15\ V$



Gate-emitter threshold voltage as a function of junction temperature, IGBT

$V_{GEth} = f(T_{vj})$

$I_C = 0.15\ mA$

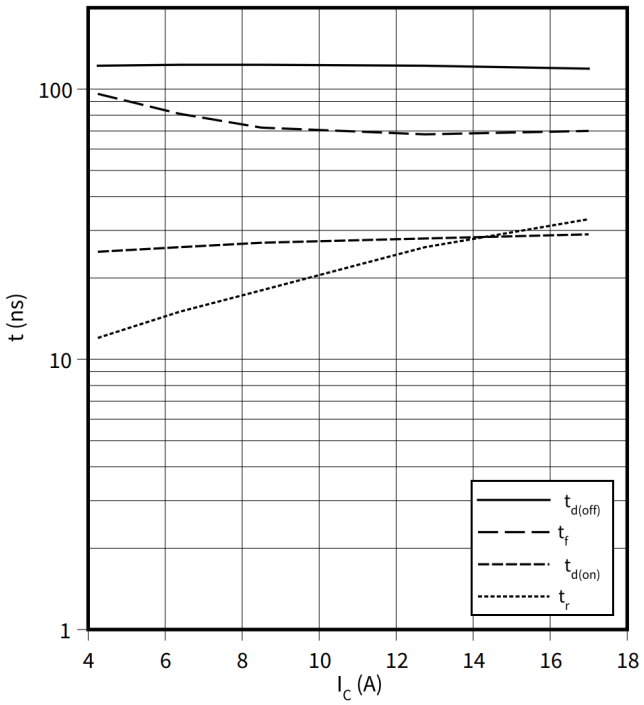


4. 特性图

Typical switching times as a function of collector current, IGBT

$t = f(I_C)$

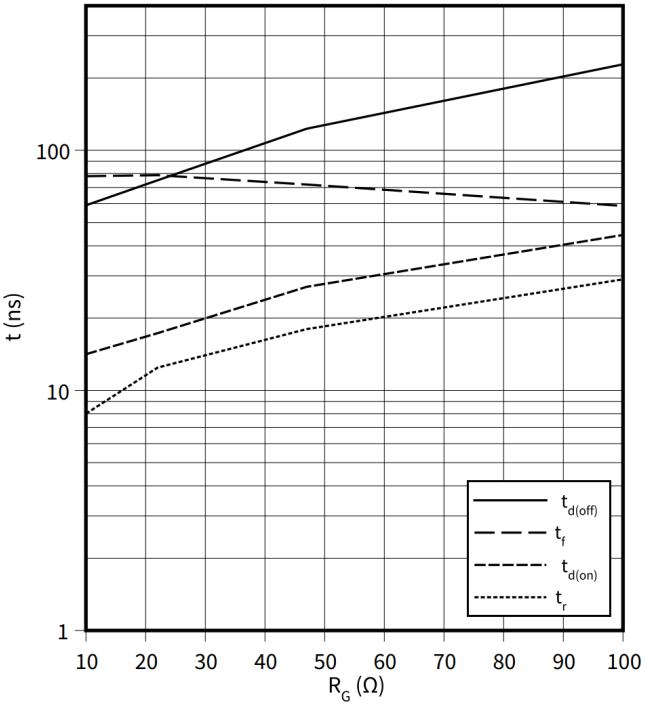
$V_{CE} = 400\ V$, $T_{vj} = 150\ °C$, $V_{GE} = 0/15\ V$, $R_G = 47\ \Omega$



Typical switching times as a function of gate resistor, IGBT

$t = f(R_G)$

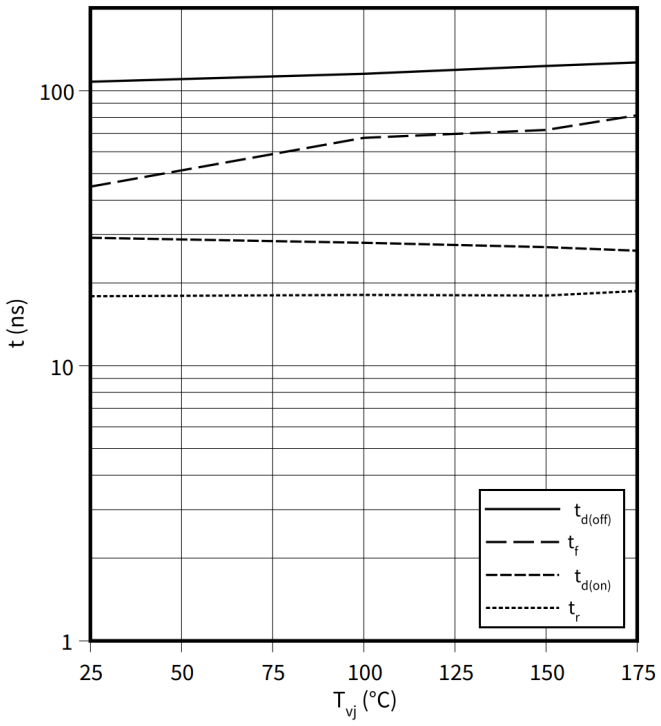
$I_C = 8.5\ A$, $V_{CE} = 400\ V$, $T_{vj} = 150\ °C$, $V_{GE} = 0/15\ V$



Typical switching times as a function of junction temperature, IGBT

$t = f(T_{vj})$

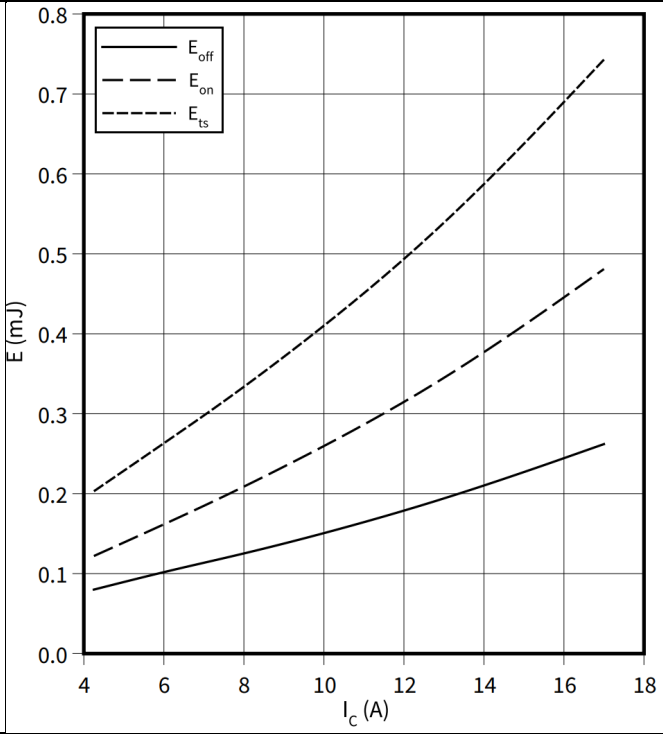
$I_C = 8.5\ A$, $V_{CE} = 400\ V$, $V_{GE} = 0/15\ V$, $R_G = 47\ \Omega$



Typical switching energy losses as a function of collector current, IGBT

$E = f(I_C)$

$V_{CE} = 400\ V$, $T_{vj} = 150\ °C$, $V_{GE} = 0/15\ V$, $R_G = 47\ \Omega$

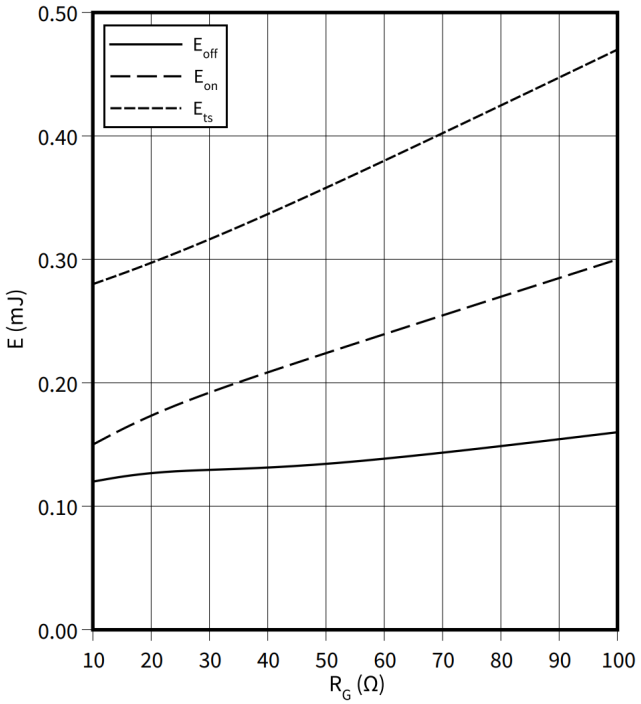


4. 特性图

Typical switching energy losses as a function of gate resistor, IGBT

$E = f(R_G)$

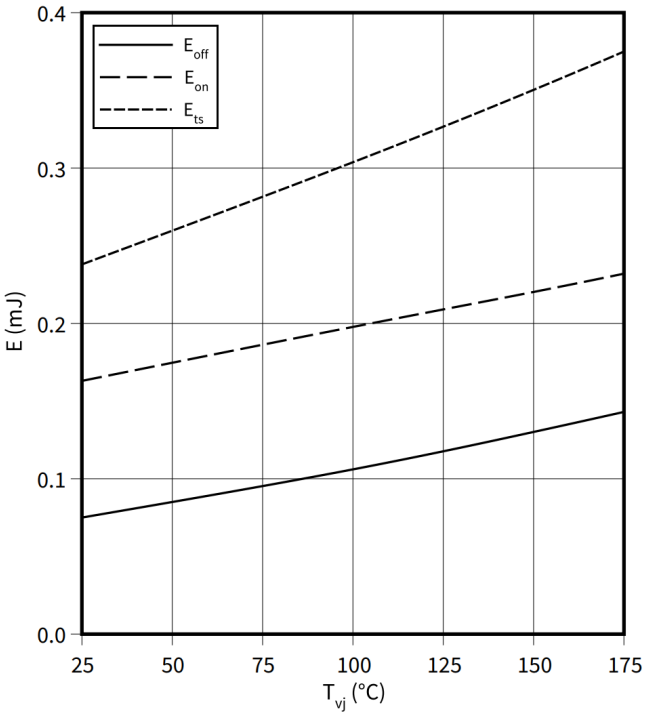
$I_C = 8.5\ A$, $V_{CE} = 400\ V$, $T_{vj} = 150\ °C$, $V_{GE} = 0/15\ V$



Typical switching energy losses as a function of junction temperature, IGBT

$E = f(T_{vj})$

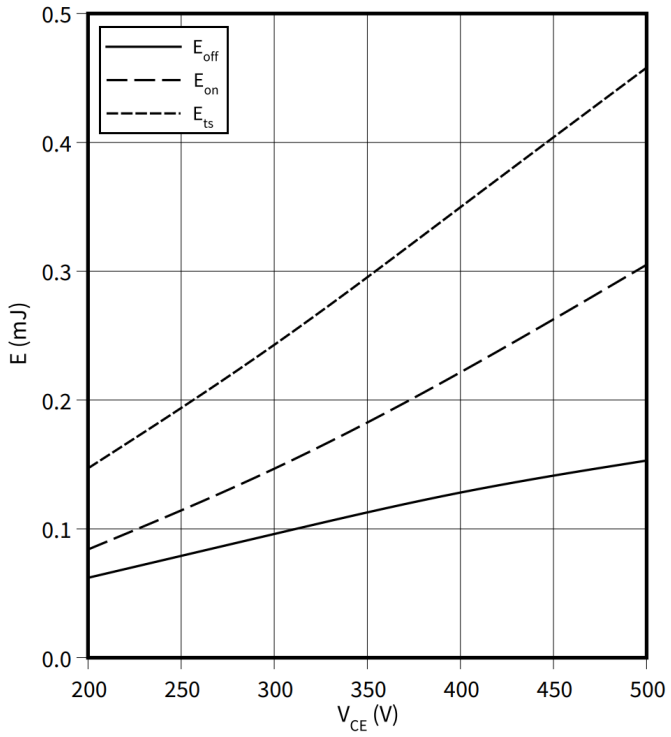
$I_C = 8.5\ A$, $V_{CE} = 400\ V$, $V_{GE} = 0/15\ V$, $R_G = 47\ Ω$



Typical switching energy losses as a function of collector emitter voltage, IGBT

$E = f(V_{CE})$

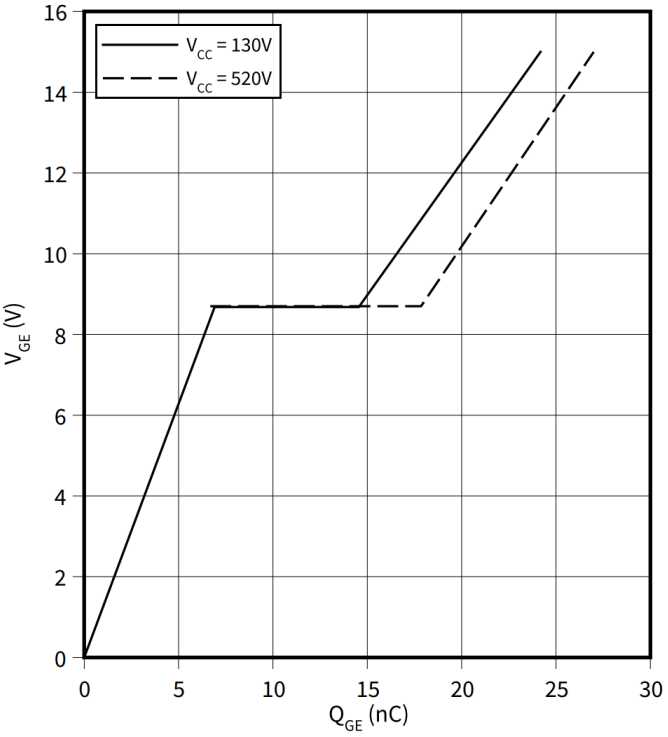
$I_C = 8.5\ A$, $V_{GE} = 0/15\ V$, $T_{vj} = 150\ °C$, $R_G = 47\ Ω$



Typical gate charge, IGBT

$V_{GE} = f(Q_{GE})$

$I_C = 8.5\ A$

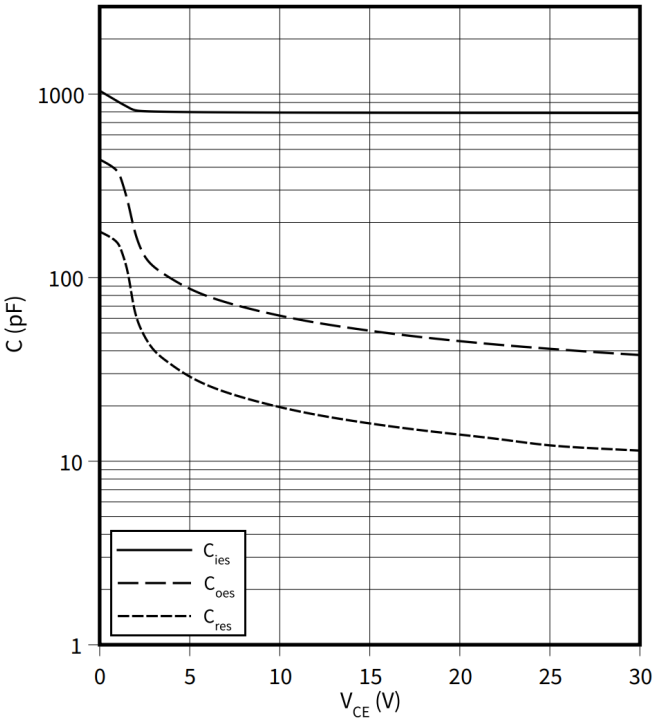


4. 特性图

Typical capacitance as a function of collector-emitter voltage, IGBT

$C = f(V_{CE})$

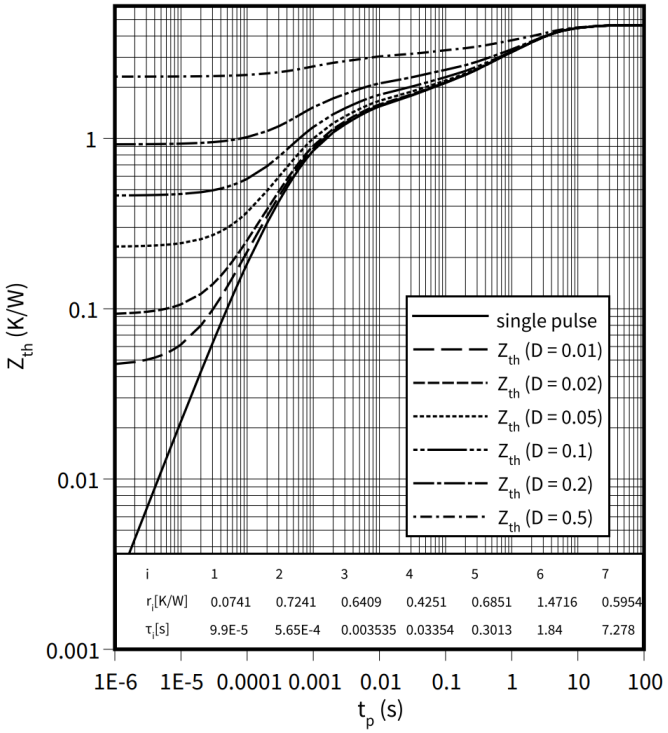
$f = 1000\ kHz$, $V_{GE} = 0\ V$



IGBT transient thermal impedance, IGBT

$Z_{th} = f(t_p)$

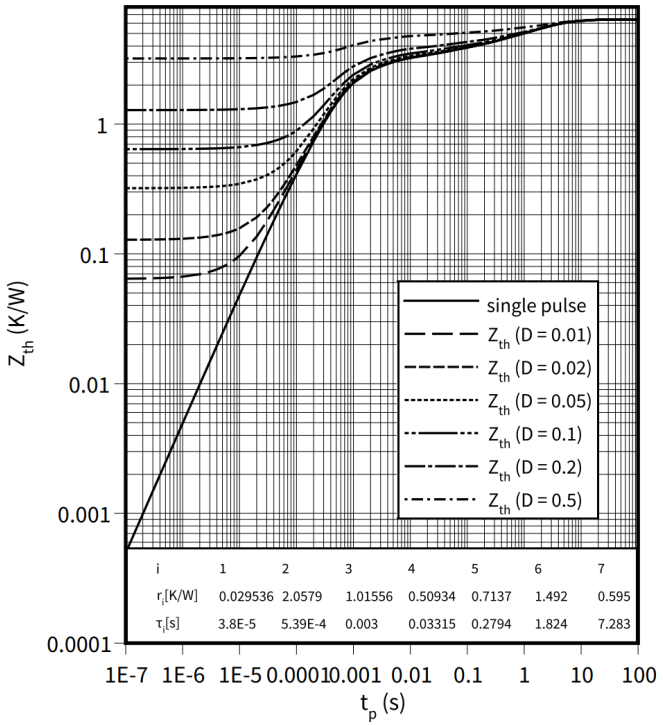
$D = t_p/T$



Diode transient thermal impedance as a function of pulse width, Diode

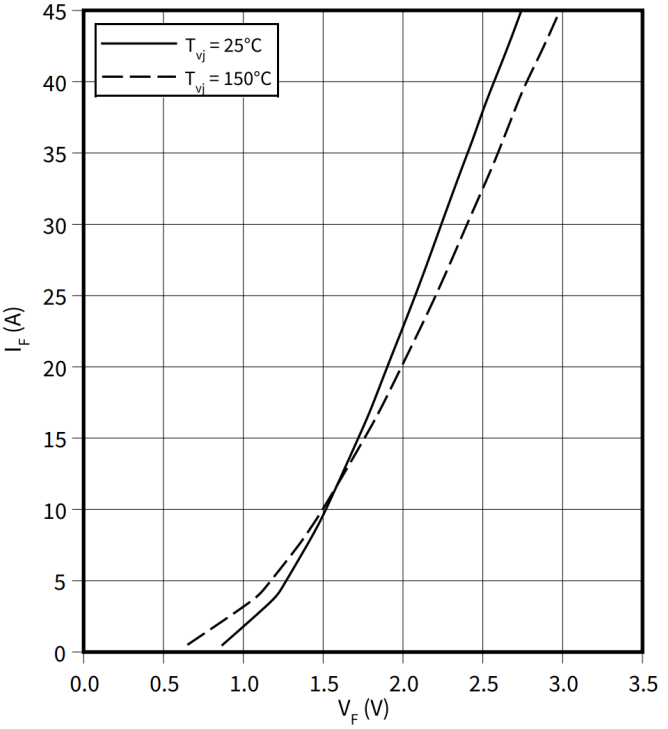
$Z_{th} = f(t_p)$

$D = t_p/T$



Typical diode forward current as a function of forward voltage, Diode

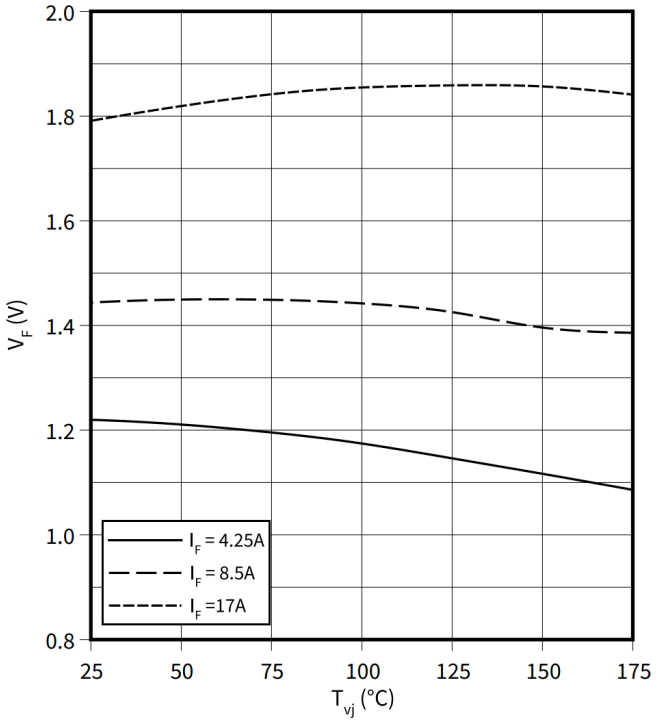
$I_F = f(V_F)$



4. 特性图

Typical diode forward voltage as a function of junction temperature, Diode

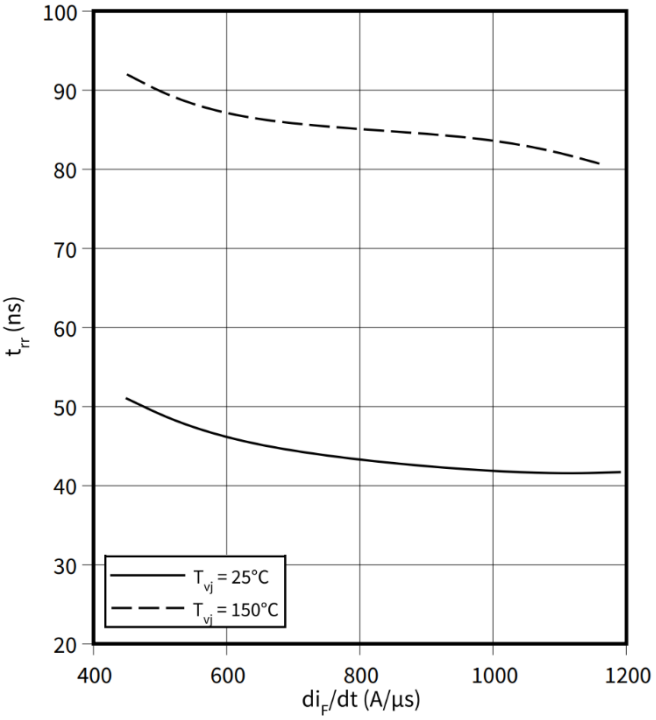
$V_F = f(T_{vj})$



Typical reverse recovery time as a function of diode current slope, Diode

$t_{rr} = f(di_F/dt)$

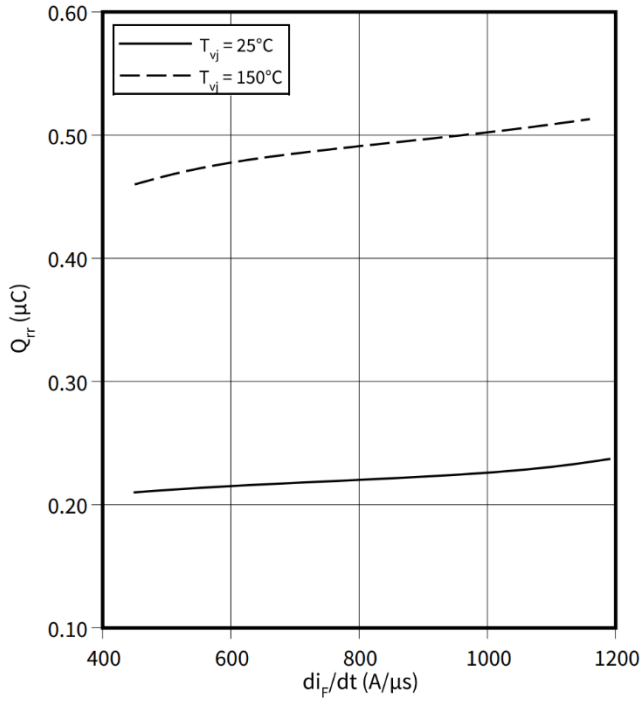
$V_R = 400\ V$, $I_F = 8.5\ A$



Typical reverse recovery charge as a function of diode current slope, Diode

$Q_{rr} = f(di_F/dt)$

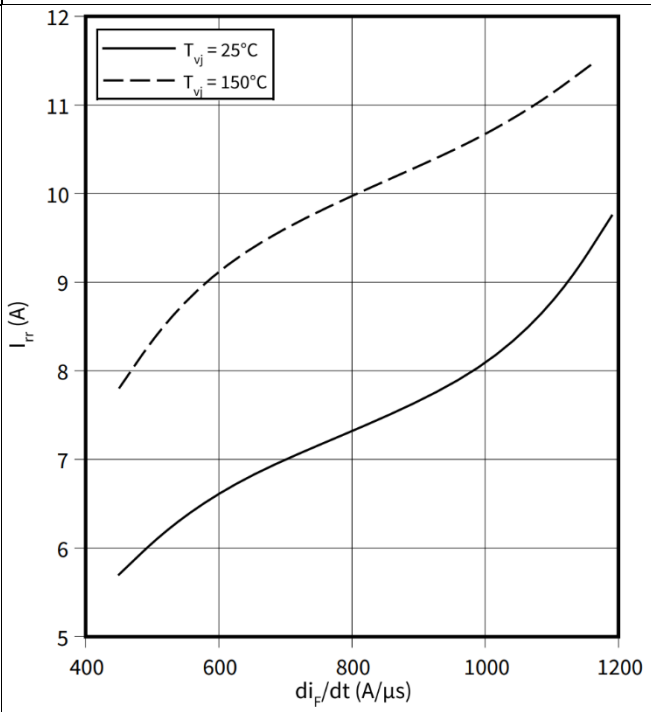
$V_R = 400\ V$, $I_F = 8.5\ A$



Typical reverse recovery current as a function of diode current slope, Diode

$I_{rr} = f(di_F/dt)$

$V_R = 400\ V$, $I_F = 8.5\ A$

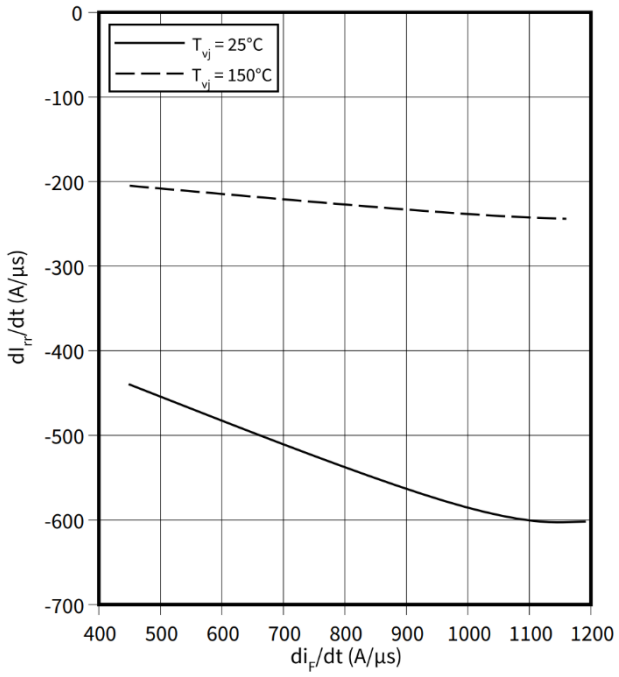


4. 特性图

Typical diode peak rate of fall of reverse recovery current as a function of diode current slope, Diode

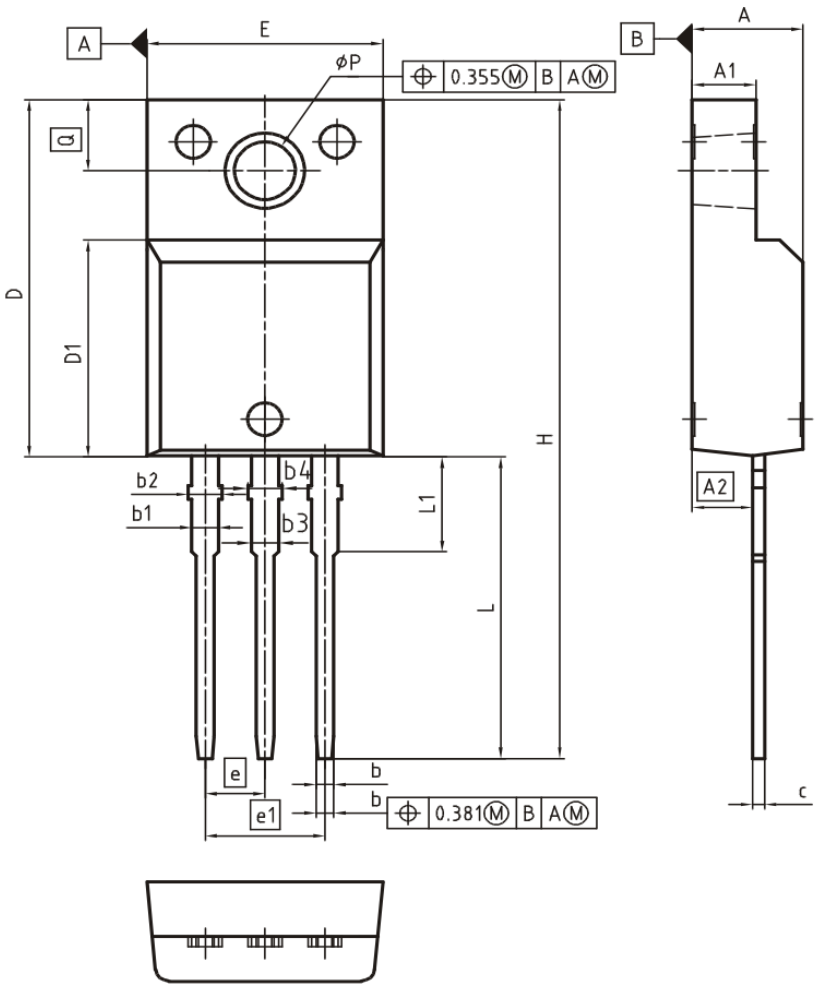
$dI_{rr}/dt = f(di_F/dt)$

$V_R = 400$ V, $I_F = 8.5$ A



5 封装外形

Package Drawing PG-TO220-3-FP



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
øP	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

DOCUMENT NO.
Z8B00003319

SCALE 0 2.5 0 2.5 5mm

EUROPEAN PROJECTION

ISSUE DATE
08-03-2007

REVISION
03

图 1

6 测试条件

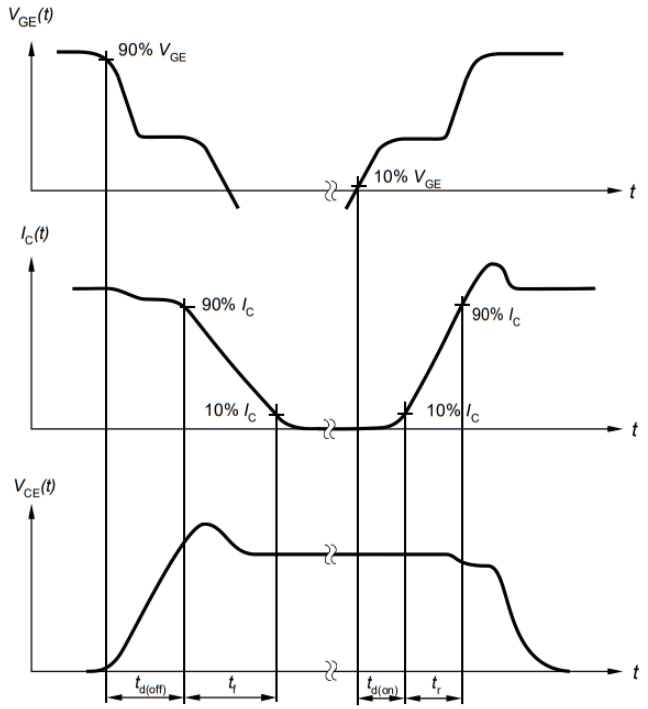


Figure A. **Definition of switching times**

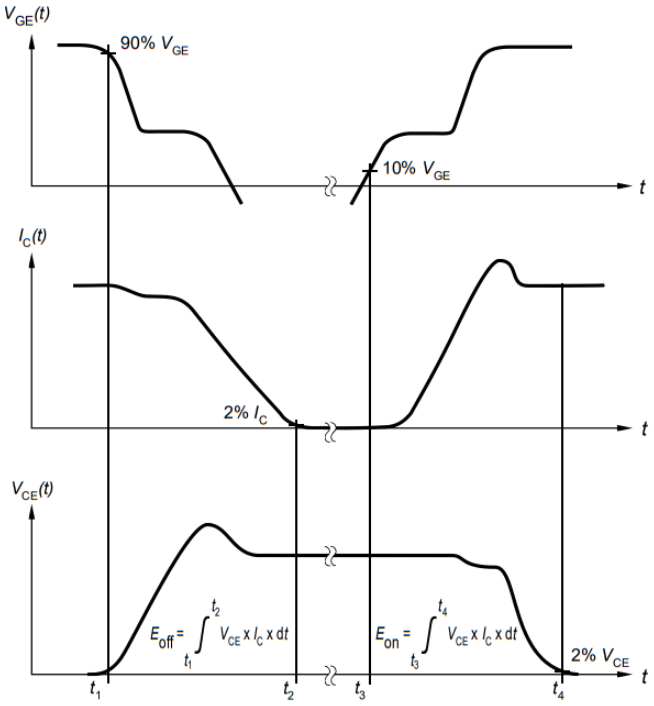


Figure B. **Definition of switching losses**

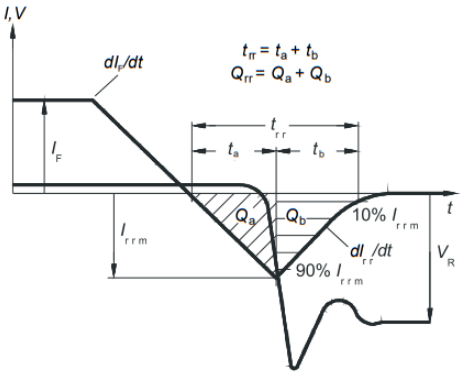


Figure C. **Definition of diode switching characteristics**

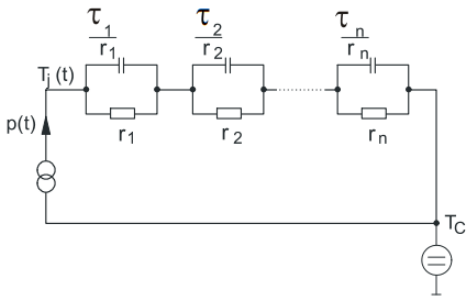


Figure D. **Thermal equivalent circuit**

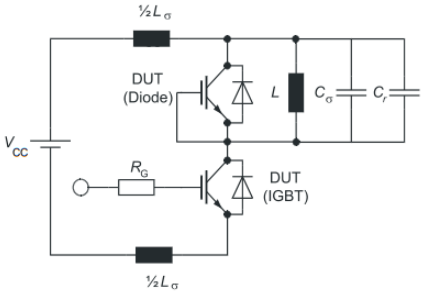


Figure E. **Dynamic test circuit**
Parasitic inductance L_σ,
parasitic capacitor C_σ,
relief capacitor C_r,
(only for ZVT switching)

图 2

修订记录

Document revision	Date of release	Description of changes
V2.1	2017-09-11	Final Datasheet
V2.2	2017-11-30	New Gfs Value at VCE=20V
V2.3	2019-09-13	Change of Rth/Zth values and maximum DC ratings
1.00	2021-10-18	Change of unit in thermal impedance figures

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